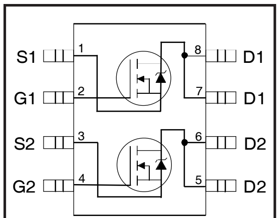
International
IOR Rectifier

PD - 95162

IRF7101PbF

HEXFET® Power MOSFET

- Adavanced Process Technology
- Ultra Low On-Resistance
- Dual N-Channel MOSFET
- Surface Mount
- Available in Tape & Reel
- Dynamic dv/dt Rating
- Fast Switching
- Lead-Free

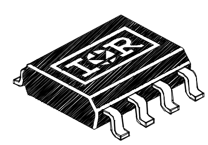


Top View

V_{DSS} = 20V

$R_{DS(on)}$ = 0.10Ω

I_D = 3.5A


SO-8

Description

Fourth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve the lowest possible on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient device for use in a wide variety of applications.

The SO-8 has been modified through a customized leadframe for enhanced thermal characteristics and dual-die capability making it ideal in a variety of power applications. With these improvements, multiple devices can be used in an application with dramatically reduced board space. The package is designed for vapor phase, infra red, or wave soldering techniques. Power dissipation of greater than 0.8W is possible in a typical PCB mount application.

Absolute Maximum Ratings

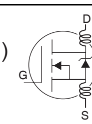
	Parameter	Max.	Units
I_D @ T_A = 25°C	Continuous Drain Current, V_{GS} @ 10V	3.5	A
I_D @ T_A = 100°C	Continuous Drain Current, V_{GS} @ 10V	2.3	
I_{DM}	Pulsed Drain Current ①	14	
P_D @T_C = 25°C	Power Dissipation	2.0	W
	Linear Derating Factor	0.016	W/°C
V_{GS}	Gate-to-Source Voltage	± 12	V
dv/dt	Peak Diode Recovery dv/dt ②	3.0	V/nS
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 150	°C
	Sodering Temperature, for 10 seconds	300(1.6mm from case)	

Thermal Resistance Ratings

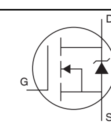
	Parameter	Min.	Typ.	Max	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient ④	——	——	62.5	°C/W

10/6/04

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	20	–––	–––	V	V_{GS} = 0V, I_D = 250μA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	–––	0.025	–––	V/°C	Reference to 25°C, I_D = 1mA
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	–––	–––	0.10	Ω	V_{GS} = 10V, I_D = 1.8A ③
		–––	–––	0.15		V_{GS} = 4.5V, I_D = 1.0A ③
$V_{GS(th)}$	Gate Threshold Voltage	1.0	–––	3.0	V	V_{DS} = V_{GS}, I_D = 250μA
g_{fs}	Forward Transconductance	1.1	–––	–––	S	V_{DS} = 15V, I_D = 3.5A ③
I_{DSS}	Drain-to-Source Leakage Current	–––	–––	2.0	μA	V_{DS} = 20V, V_{GS} = 0V
		–––	–––	250		V_{DS} = 16V, V_{GS} = 0V, T_J = 125 °C
I_{GSS}	Gate-to-Source Forward Leakage	–––	–––	100	nA	V_{GS} = 12V
	Gate-to-Source Reverse Leakage	–––	–––	-100		V_{GS} = - 12V
Q_g	Total Gate Charge	–––	–––	15	nC	I_D = 1.8A
Q_{gs}	Gate-to-Source Charge	–––	–––	2.0		V_{DS} = 16V
Q_{gd}	Gate-to-Drain ("Miller") Charge	–––	–––	3.6		V_{GS} = 10V
$t_{d(on)}$	Turn-On Delay Time	–––	7.0	–––	ns	V_{DD} = 10V
t_r	Rise Time	–––	10	–––		I_D = 1.8A
$t_{d(off)}$	Turn-Off Delay Time	–––	24	–––		R_G = 8.2Ω
t_f	Fall Time	–––	30	–––		R_D = 26Ω
L_D	Internal Drain Inductance	–––	4.0	–––	nH	Between lead,6mm(0.25in.) from package and center of die contact 
L_S	Internal Source Inductance	–––	6.0	–––		
C_{iss}	Input Capacitance	–––	320	–––	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	–––	250	–––		V_{DS} = 15V
C_{rss}	Reverse Transfer Capacitance	–––	75	–––		f = 1.0MHz

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	–––	–––	2.0	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	–––	–––	14		
V_{SD}	Diode Forward Voltage	–––	–––	1.2	V	T_J = 25°C, I_S = 1.7A, V_{GS} = 0V ③
t_{rr}	Reverse Recovery Time	–––	36	54	ns	T_J = 25°C, I_F = 1.7A
Q_{rr}	Reverse RecoveryCharge	–––	41	62	nC	di/dt = 100A/μs ③
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Notes:

① Repetitive rating; pulse width limited by max. junction temperature.

② $I_{SD} \le$ 3.5A, di/dt $\le$ 90A/μs, $V_{DD} \le V_{(BR)DSS}$, $T_J \le$ 150°C

③ Pulse width $\le$ 300μs; duty cycle $\le$ 2%.

④ Surface mounted on FR-4 board, t $\le$ 10sec.

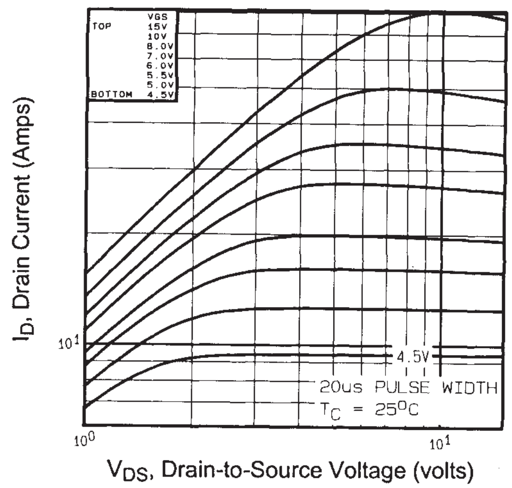


Fig 1. Typical Output Characteristics,

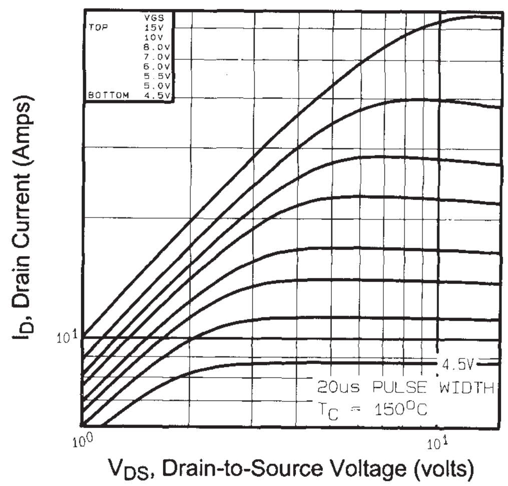


Fig 2. Typical Output Characteristics,

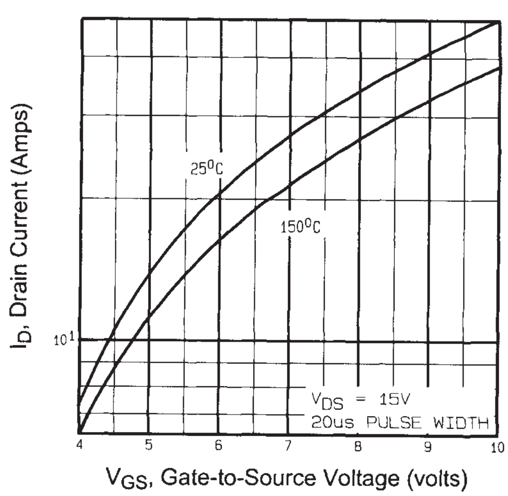


Fig 3. Typical Transfer Characteristics

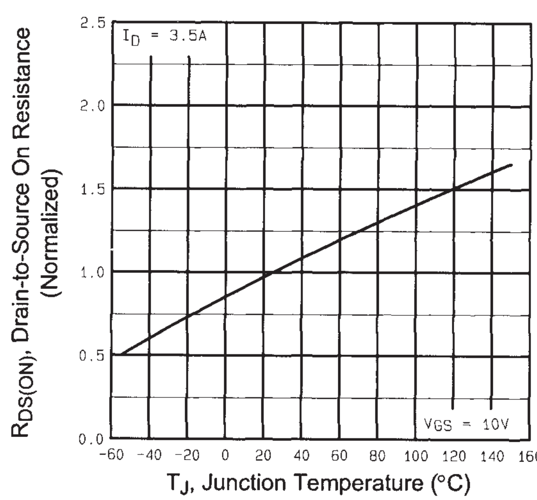


Fig 4. Normalized On-Resistance Vs. Temperature

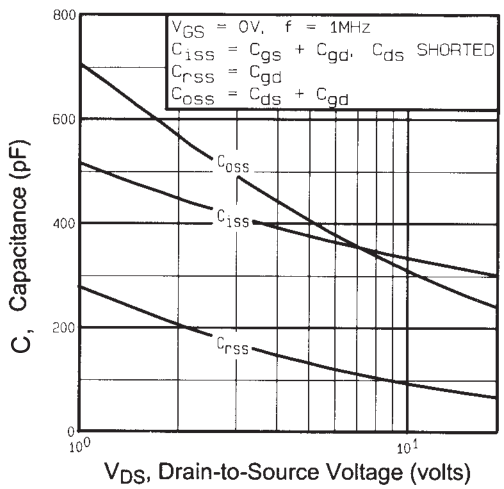


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

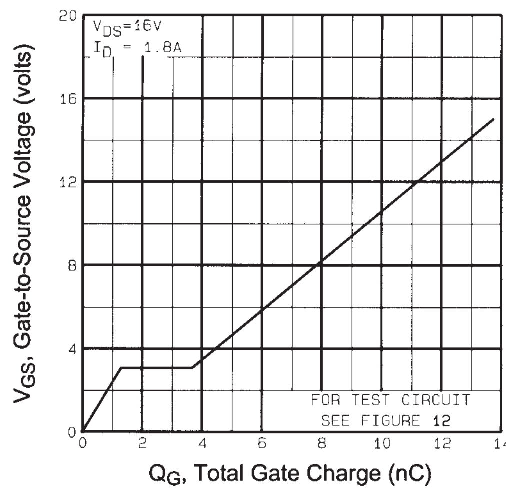


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

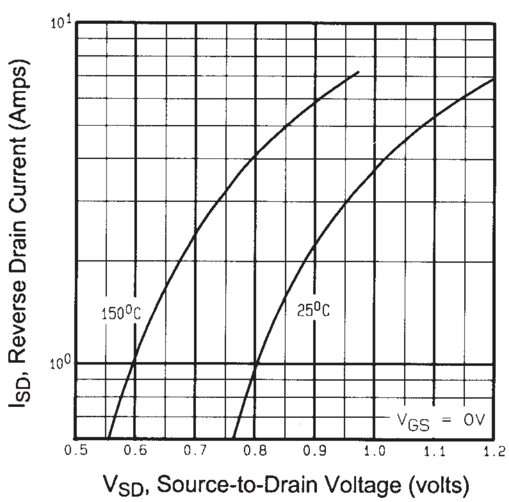


Fig 7. Typical Source-Drain Diode Forward Voltage

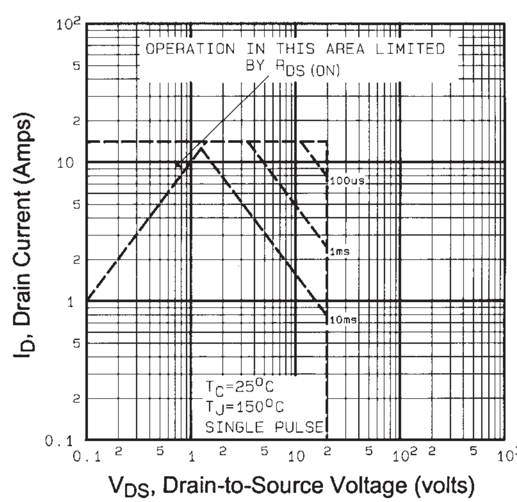


Fig 8. Maximum Safe Operating Area

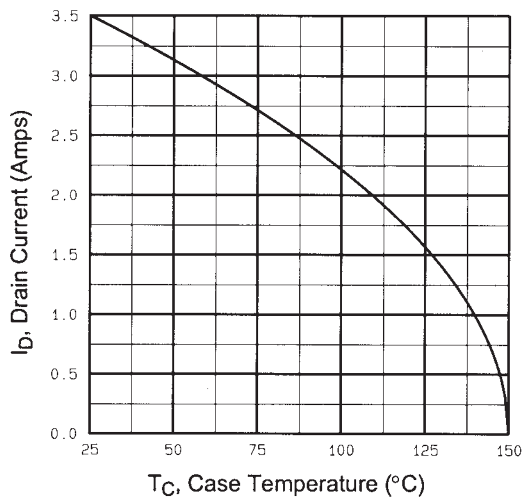


Fig 9. Maximum Drain Current Vs. Case Temperature

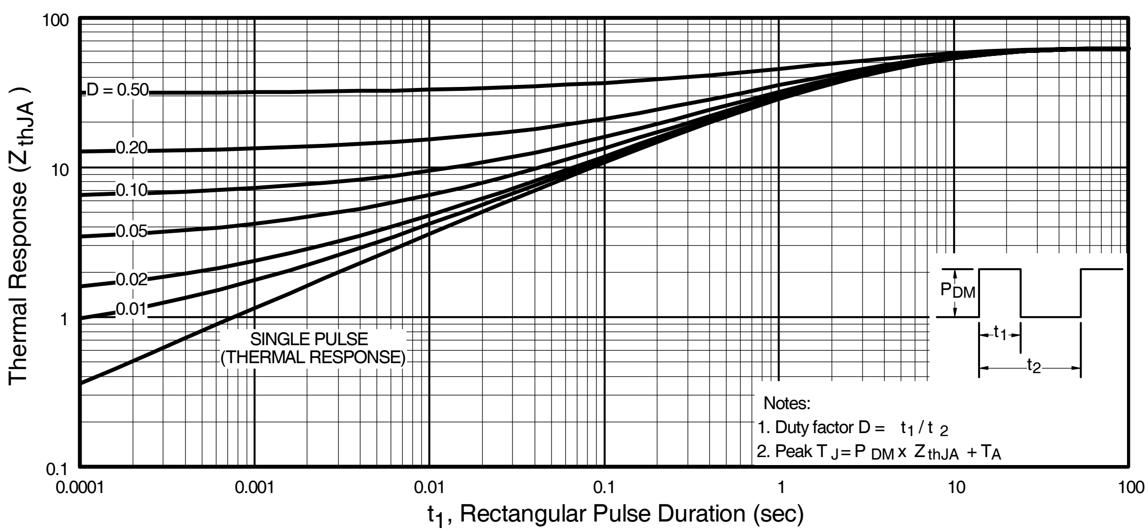


Fig 10. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

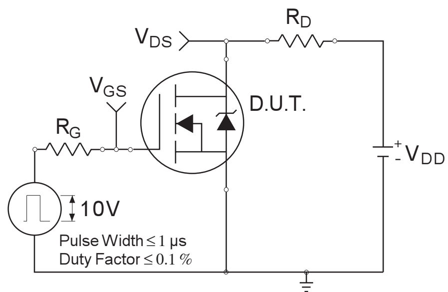


Fig 11a. Switching Time Test Circuit

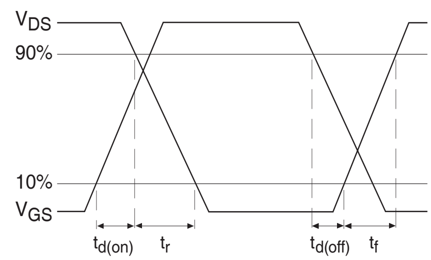


Fig 11b. Switching Time Waveforms

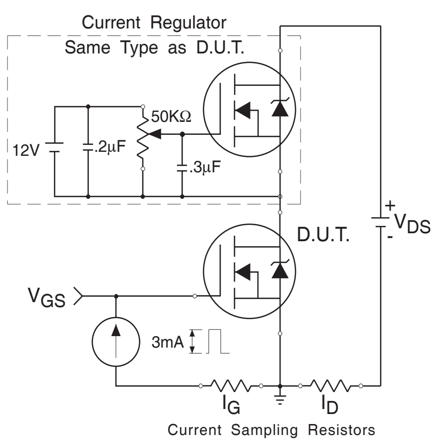


Fig 12a. Gate Charge Test Circuit

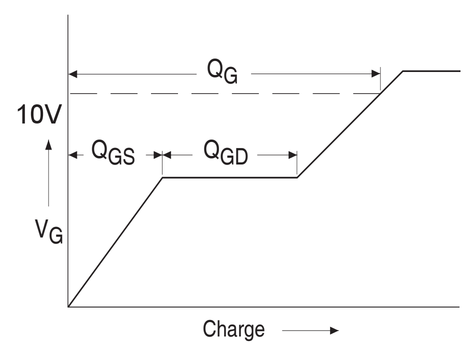
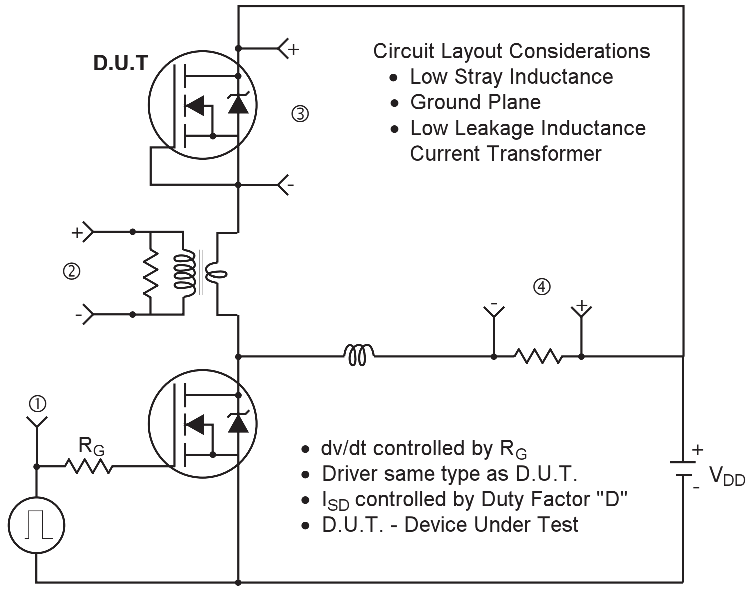
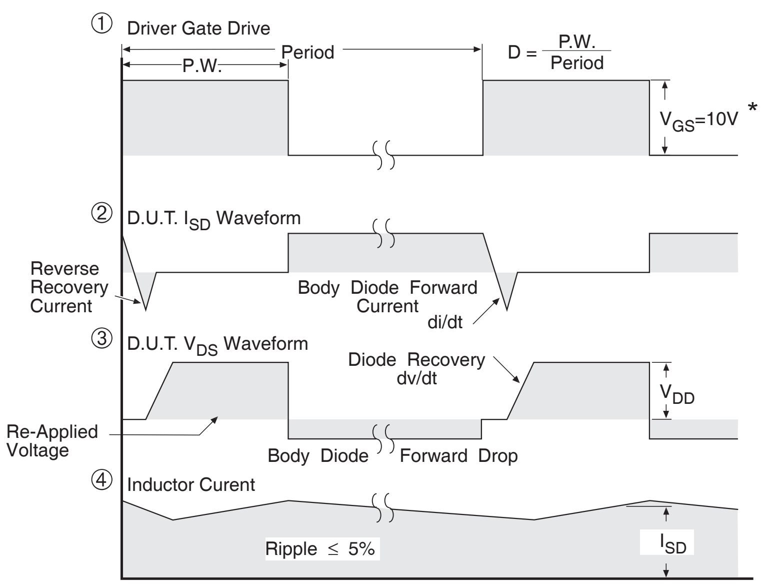


Fig 12b. Basic Gate Charge Waveform

Peak Diode Recovery dv/dt Test Circuit



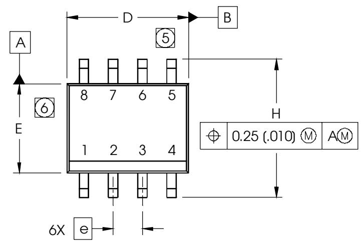


* VGS = 5V for Logic Level Devices

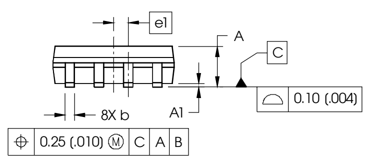
Fig 13. For N-Channel HEXFETS

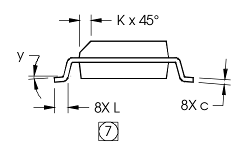
SO-8 Package Outline

Dimensions are shown in milimeters (inches)



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°





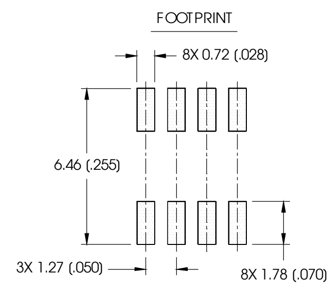
NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.

5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [.006].

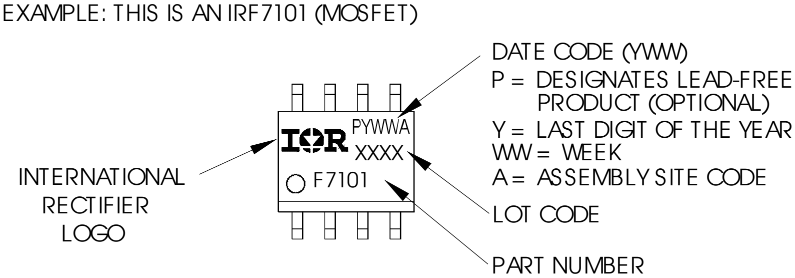
6. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [.010].

7. DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.



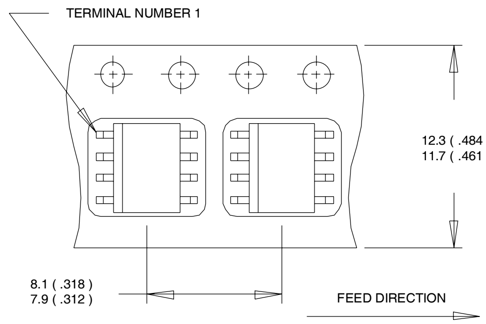
SO-8 Part Marking Information (Lead-Free)

EXAMPLE: THIS IS AN IRF7101 (MOSFET)

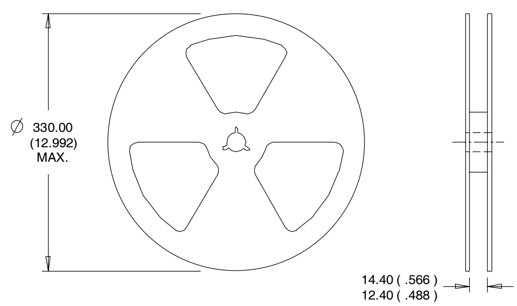


SO-8 Tape and Reel

Dimensions are shown in milimeters (inches)



NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Data and specifications subject to change without notice.
This product has been designed and qualified for the Consumer market.
Qualifications Standards can be found on IR's Web site.

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